

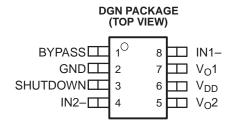


Check for Samples: TPA6110A2

FEATURES

- 150 mW Stereo Output
- PC Power Supply Compatible
 - Fully Specified for 3.3 V and 5 V Operation
 - Operation to 2.5 V
- Pop Reduction Circuitry
- · Internal Mid-Rail Generation
- · Thermal and Short-Circuit Protection

- Surface-Mount Packaging
 - PowerPAD™ MSOP
- Pin Compatible With LM4881

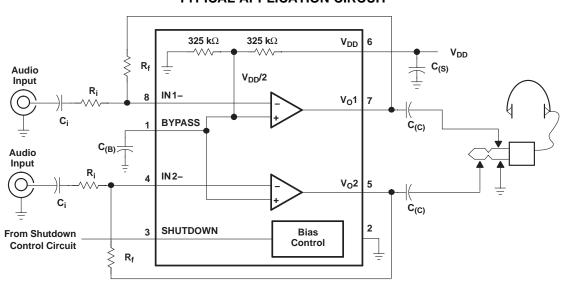


DESCRIPTION

The TPA6110A2 is a stereo audio power amplifier packaged in an 8-pin PowerPAD™ MSOP package capable of delivering 150 mW of continuous RMS power per channel into 16-Ω loads. Amplifier gain is externally configured by means of two resistors per input channel and does not require external compensation for settings of 1 to 10.

THD+N when driving a 16- Ω load from 5 V is 0.03% at 1 kHz, and less than 1% across the audio band of 20 Hz to 20 kHz. For 32- Ω loads, the THD+N is reduced to less than 0.02% at 1 kHz, and is less than 1% across the audio band of 20 Hz to 20 kHz. For 10-k Ω loads, the THD+N performance is 0.005% at 1 kHz, and less than 0.5% across the audio band of 20 Hz to 20 kHz.

TYPICAL APPLICATION CIRCUIT



M

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

PowerPAD is a trademark of Texas Instruments.





These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

AVAILABLE OPTIONS

т	PACKAGED DEVICE	MSOP SYMBOLIZATION
I A	MSOP ⁽¹⁾	MSOP STMBOLIZATION
-40°C to 85°C	TPA6110A2DGN	TI AIZ

(1) The DGN package is available in left-ended tape and reel only (e.g., TPA6110A2DGNR).

PinFunctions

PIN		1/0	DESCRIPTION	
NAME	NO.	1/0	DESCRIPTION	
BYPASS	1	I	Tap to voltage divider for internal mid-supply bias supply. Connect to a 0.1 μ F to 1 μ F low ESR capacitor for best performance.	
GND	2	- 1	GND is the ground connection.	
IN1-	8	I	IN1– is the inverting input for channel 1.	
IN2-	4	I	IN2– is the inverting input for channel 2.	
SHUTDOWN	3	- 1	Puts the device in a low quiescent current mode when held high.	
V_{DD}	6	- 1	V _{DD} is the supply voltage terminal.	
V _O 1	7	0	V _O 1 is the audio output for channel 1.	
V _O 2	5	0	V _O 2 is the audio output for channel 2.	

ABSOLUTE MAXIMUM RATINGS(1)

over operating free-air temperature range (unless otherwise noted)

		UNIT
V_{DD}	Supply voltage	6 V
V_{I}	Input voltage	–0.3 V to V _{DD} + 0.3 V
	Continuous total power dissipation	Internally limited
T _J	Operating junction temperature range	-40°C to 150°C
T _{stg}	Storage temperature range	-65°C to 150°C

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

DISSIPATION RATING TABLE

PACKAGE	T _A ≤ 25°C	DERATING FACTOR	T _A = 70°C	T _A = 85°C
	POWER RATING	ABOVE T _A = 25°C	POWER RATING	POWER RATING
DGN	2.14 W ⁽¹⁾	17.1 mW/°C	1.37 W	1.11 W

⁽¹⁾ See the Texas Instruments document, PowerPAD Thermally Enhanced Package Application Report (SLMA002), for more information on the PowerPAD™ package. The thermal data was measured on a PCB layout based on the information in the section entitled Texas Instruments Recommended Board for PowerPAD on page 33 of the before mentioned document.

RECOMMENDED OPERATING CONDITIONS

	MINIERDED OF ERVATING CONDITIONS			
		MIN	MAX	UNIT
V_{DD}	Supply voltage	2.5	5.5	V
T_A	Operating free-air temperature	-40	85	°C
V_{IH}	High-level input voltage (SHUTDOWN)	60% x V _{DD}		V
V_{IL}	Low-level input voltage (SHUTDOWN)		25% x V _{DD}	V

Product Folder Link(s): TPA6110A2



DC ELECTRICAL CHARACTERISTICS

at $T_A = 25$ °C, $V_{DD} = 2.5$ V (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Voo	Output offset voltage	$A_V = 2 \text{ V/V}$			15	mV
PSRR	Power supply rejection ratio	V _{DD} = 3.2 V to 3.4 V		83		dB
I _{DD}	Supply current	SHUTDOWN = 0 V		1.5	3	mA
I _{DD(SD)}	Supply current in shutdown mode	SHUTDOWN = V _{DD}		1	10	μΑ

AC OPERATING CHARACTERISTICS

 $V_{DD} = 3.3 \text{ V}, T_A = 25^{\circ}\text{C}, R_L = 16 \Omega$

	PARAMETER	TEST CONDITIONS	MIN TYP MAX	UNIT
Po	Output power (each channel)	THD≤ 0.1%, f = 1 kHz	60	mW
THD+N	Total harmonic distortion + noise	P _O = 40 mW, 20 - 20 kHz	0.4%	
B _{OM}	Maximum output power BW	G = 10, THD < 5%	> 20	kHz
	Phase margin	Open loop	96°	
	Supply ripple rejection ratio	f = 1 kHz	71	dB
	Channel/channel output separation	f = 1 kHz, P _O = 40 mW	89	dB
SNR	Signal-to-noise ratio	P _O = 50 mW, A _V = 1	100	dB
V _n	Noise output voltage	A _V = 1	11	μV(rms)

DC ELECTRICAL CHARACTERISTICS

at $T_A = 25^{\circ}C$, $V_{DD} = 5.5 \text{ V}$ (unless otherwise noted)

αι · _A – 2	t TA = 20 G, VDD = 6.6 V (arriced enterwise flower)							
	PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT			
Voo	Output offset voltage	A _V = 2 V/V		15	mV			
PSRR	Power supply rejection ratio	V _{DD} = 4.9 V to 5.1 V	76		dB			
I _{DD}	Supply current	SHUTDOWN = 0 V	1.5	3	mA			
I _{DD(SD)}	Supply current in shutdown mode	SHUTDOWN = V _{DD}	1	10	μΑ			
I _{IH}	High-level input current (SHUTDOWN)	$V_{DD} = 5.5 \text{ V}, V_I = V_{DD}$		1	μΑ			
I _{IL}	Low-level input current (SHUTDOWN)	V _{DD} = 5.5 V, V _I = 0 V		1	μΑ			
Zi	Input impedance		>1		МΩ			

AC OPERATING CHARACTERISTICS

 $V_{DD} = 5 \text{ V. } T_{\Lambda} = 25^{\circ}\text{C. } R_{L} = 16 \Omega$

V _{DD} = 0 V, I _A = 20 G, I _C = 10 12						
	PARAMETER	TEST CONDITIONS	MIN TYP MAX	UNIT		
Po	Output power (each channel)	THD≤ 0.1%, f = 1 kHz	150	mW		
THD+N	Total harmonic distortion + noise	P _O = 100 mW, 20 - 20 kHz	0.6%			
B _{OM}	Maximum output power BW	G = 10, THD < 5%	> 20	kHz		
	Phase margin	Open loop	96°			
	Supply ripple rejection ratio	f = 1 kHz	61	dB		
	Channel/Channel output separation	f = 1 kHz, P _O = 100 mW	90	dB		
SNR	Signal-to-noise ratio	P _O = 100 mW, A _V = 1	100	dB		
V _n	Noise output voltage	A _V = 1	11.7	μV(rms)		

AC OPERATING CHARACTERISTICS

 $V_{DD} = 3.3 \text{ V}, T_A = 25^{\circ}\text{C}, R_L = 32 \Omega$

PARAME	TER	TEST CONDITIONS	MIN TYP MAX	UNIT
Po	Output power (each channel)	THD≤ 0.1%, f = 1 kHz	40	mW
THD+N	Total harmonic distortion + noise	P _O = 30 mW, 20 - 20 kHz	0.4%	
B _{OM}	Maximum output power BW	A _V = 10, THD < 2%	> 20	kHz

Copyright © 2000–2011, Texas Instruments Incorporated



AC OPERATING CHARACTERISTICS (continued)

 $V_{DD}=3.3~V,~T_A=25^{\circ}C,~R_L=32~\Omega$

PARAM	IETER	TEST CONDITIONS	MIN TYP	MAX UN	NIT
	Phase margin	Open loop	96°		
	Supply ripple rejection ratio	f = 1 kHz	71	d	ΙB
	Channel/channel output separation	f = 1 kHz	95	d	ΙB
SNR	Signal-to-noise ratio	$P_{O} = 40 \text{ mW}, A_{V} = 1$	100	d	ΙB
V _n	Noise output voltage	A _V = 1	11	μV(ı	rms)

AC OPERATING CHARACTERISTICS

 V_{DD} = 5 V, T_A = 25°C, R_L = 32 Ω

PARAME	TER	TEST CONDITIONS	MIN TYP MAX	UNIT
Po	Output power (each channel)	THD≤ 0.1%, f = 1 kHz	90	mW
THD+N	Total harmonic distortion + noise	$P_0 = 60 \text{ mW}, 20 - 20 \text{ kHz}$	0.4%	
B _{OM}	Maximum output power BW	A _V = 10, THD < 2%	> 20	kHz
	Phase margin	Open loop	97°	
	Supply ripple rejection ratio	f = 1 kHz	61	dB
	Channel/channel output separation	f = 1 kHz	98	dB
SNR	Signal-to-noise ratio	$P_{O} = 90 \text{ mW}, A_{V} = 1$	100	dB
V _n	Noise output voltage	A _V = 1	11.7	μV(rms)

TYPICAL CHARACTERISTICS

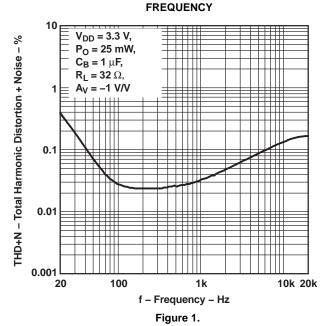
Table of Graphs

			FIGURE		
THD+N	Total harmonia distortion plus poiss	vs Frequency	1, 3, 5, 6, 7, 9, 11, 13		
I HD+N	Total harmonic distortion plus noise	vs Output power	2, 4, 8, 10, 12, 14		
	Supply ripple rejection ratio	vs Frequency	15, 16		
V _n	Output noise voltage	vs Frequency	17, 18		
	Crosstalk	vs Frequency	19–24		
	Shutdown attenuation	vs Frequency	25, 26		
	Open-loop gain and phase margin	vs Frequency	27, 28		
	Output power	vs Load resistance	29, 30		
I _{DD}	Supply current	vs Supply voltage	31		
SNR	Signal-to-noise ratio	vs Voltage gain	32		
· · · · · · · · · · · · · · · · · · ·	Power dissipation/amplifier	vs Load power	33, 34		

Submit Documentation Feedback



TOTAL HARMONIC DISTORTION + NOISE vs



TOTAL HARMONIC DISTORTION + NOISE vs OUTPUT POWER

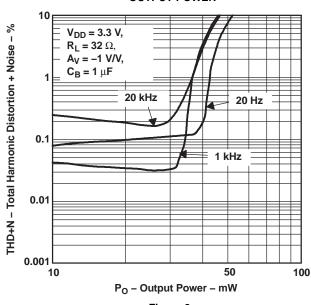
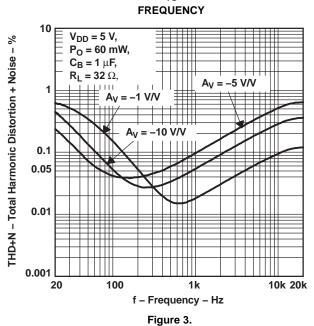


Figure 2.

TOTAL HARMONIC DISTORTION + NOISE



TOTAL HARMONIC DISTORTION + NOISE

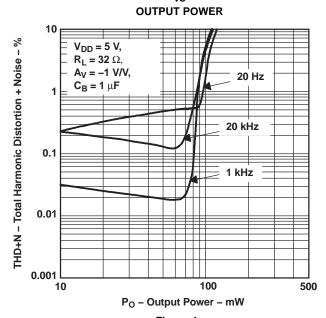
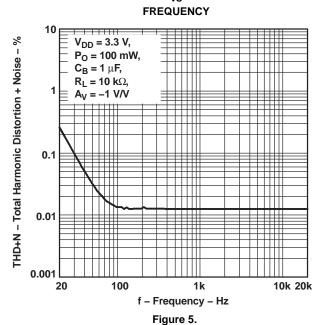


Figure 4.



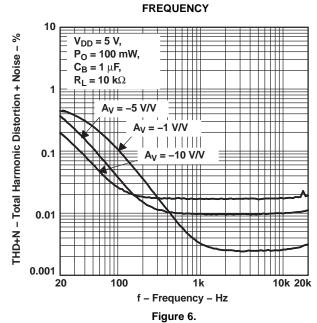
TOTAL HARMONIC DISTORTION + NOISE



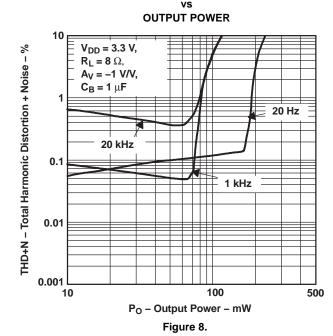
TOTAL HARMONIC DISTORTION + NOISE vs

FREQUENCY 10 ----THD+N - Total Harmonic Distortion + Noise - % $V_{DD} = 3.3 V,$ $P_0 = 60 \text{ mW},$ $C_B = 1 \mu F$, $R_L = 8 \Omega$ = -1 V/V0.1 0.01 0.001 20 100 1k 10k 20k f - Frequency - Hz Figure 7.

TOTAL HARMONIC DISTORTION + NOISE vs

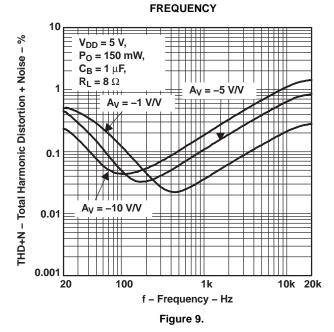


TOTAL HARMONIC DISTORTION + NOISE

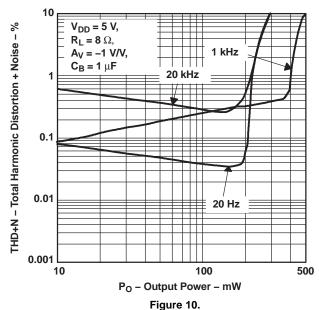




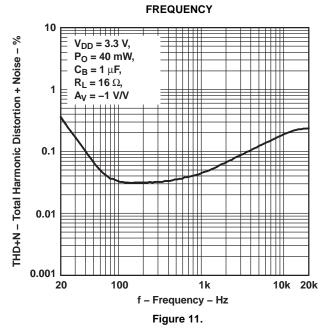
TOTAL HARMONIC DISTORTION + NOISE vs



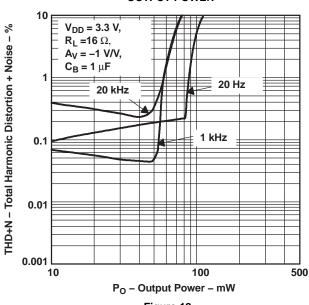
TOTAL HARMONIC DISTORTION + NOISE vs OUTPUT POWER



TOTAL HARMONIC DISTORTION + NOISE vs



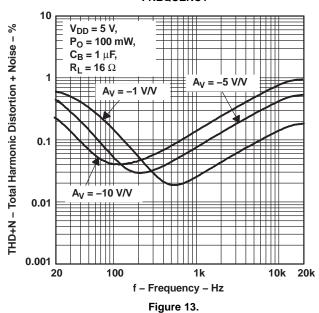
TOTAL HARMONIC DISTORTION + NOISE vs OUTPUT POWER



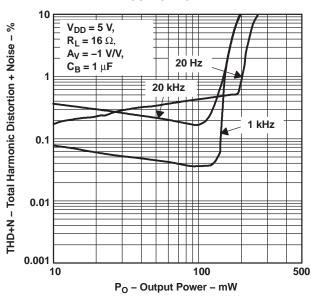


TOTAL HARMONIC DISTORTION + NOISE

FREQUENCY

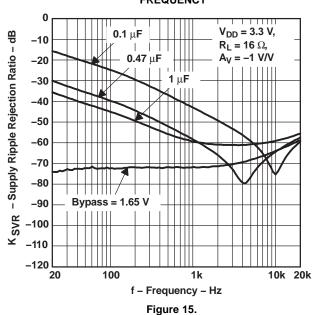


TOTAL HARMONIC DISTORTION + NOISE vs OUTPUT POWER



SUPPLY RIPPLE REJECTION RATIO

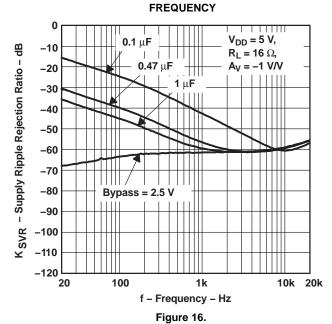
FREQUENCY



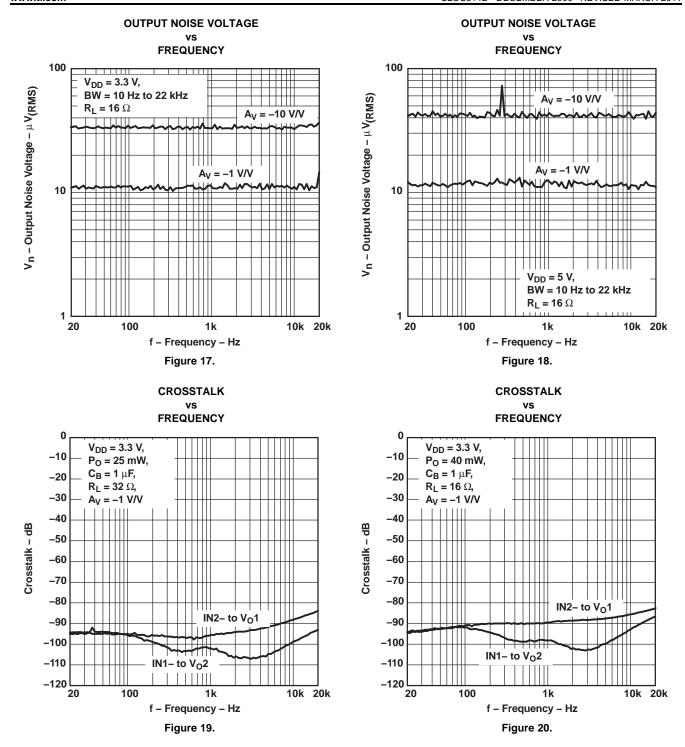
SUPPLY RIPPLE REJECTION RATIO

Figure 14.

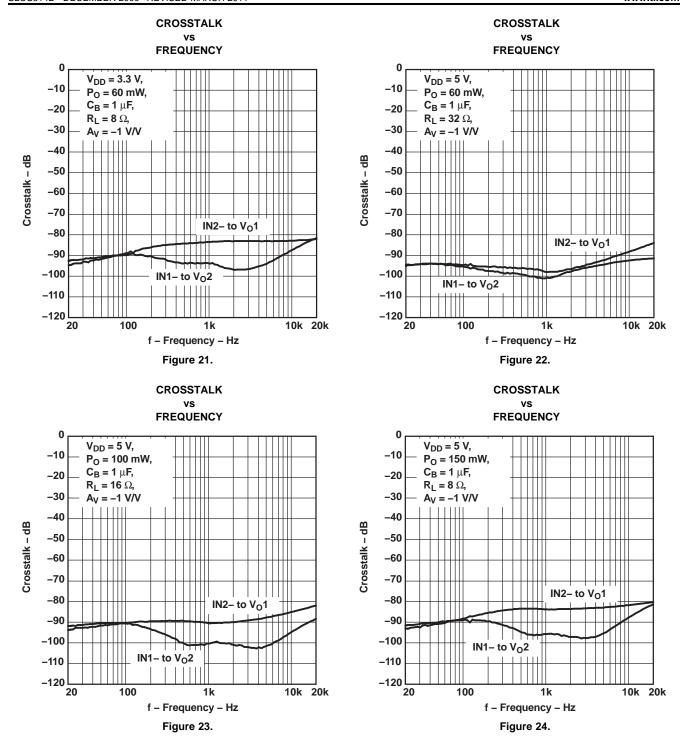
VS











SHUTDOWN ATTENUATION



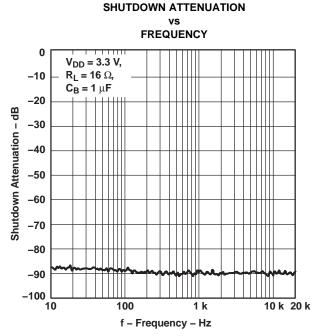


Figure 25.

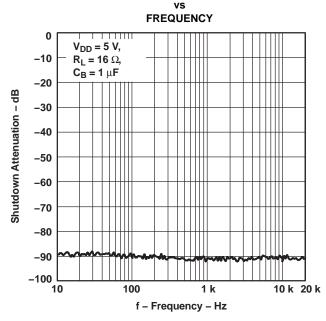
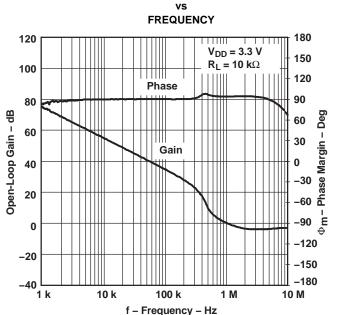


Figure 26.

OPEN-LOOP GAIN AND PHASE MARGIN



OPEN-LOOP GAIN AND PHASE MARGIN

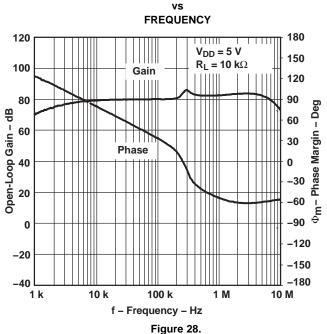
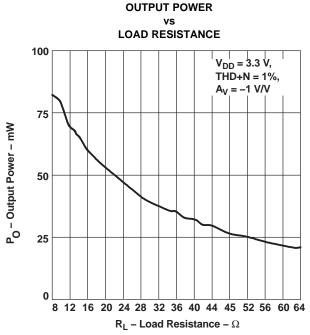
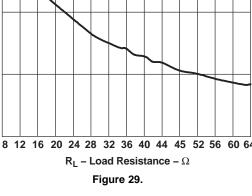
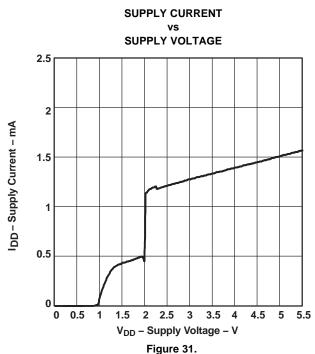


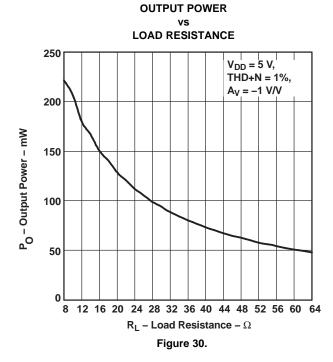
Figure 27.

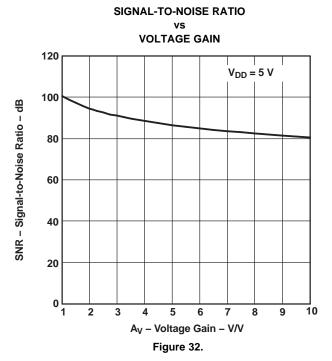






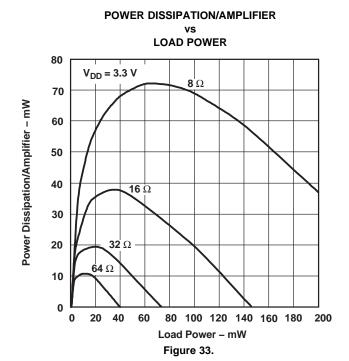


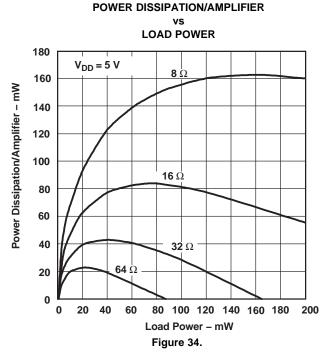




Submit Documentation Feedback









APPLICATION INFORMATION

GAIN SETTING RESISTORS, R_f and R_i

The gain for the TPA6110A2 is set by resistors R_f and R_i according to Equation 1.

$$Gain = -\left(\frac{R_f}{R_i}\right)$$
 (1)

Given that the TPA6110A2 is a MOS amplifier, the input impedance is very high. Consequently input leakage currents are not generally a concern. However, noise in the circuit increases as the value of $R_{\rm f}$ increases. In addition, a certain range of $R_{\rm f}$ values is required for proper start-up operation of the amplifier. Considering these factors, it is recommended that the effective impedance seen by the inverting node of the amplifier be set between 5 $k\Omega$ and 20 $k\Omega$. The effective impedance is calculated using Equation 2.

Effective Impedance =
$$\frac{R_f R_i}{R_f + R_i}$$
 (2)

For example, if the input resistance is 20 $k\Omega$ and the feedback resistor is 20 $k\Omega,$ the gain of the amplifier is -1, and the effective impedance at the inverting terminal is 10 $k\Omega,$ a value within the recommended range.

For high performance applications, metal-film resistors are recommended because they tend to have lower noise levels than carbon resistors. For values of $R_{\rm f}$ above 50 k Ω , the amplifier tends to become unstable due to a pole formed from $R_{\rm f}$ and the inherent input capacitance of the MOS input structure. For this reason, a small compensation capacitor of approximately 5 pF should be placed in parallel with $R_{\rm f}$. This, in effect, creates a low-pass filter network with the cutoff frequency defined by Equation 3.

$$f_{c(lowpass)} = \frac{1}{2\pi R_f C_F}$$
 (3)

For example, if R_f is 100 $k\Omega$ and C_F is 5 pF then $f_{c(lowpass)}$ is 318 kHz, which is well outside the audio range.

INPUT CAPACITOR, Ci

In the typical application, an input capacitor, C_i , is required to allow the amplifier to bias the input signal to the proper dc level for optimum operation. In this case, C_i and R_i form a high-pass filter with the corner frequency determined in Equation 4.

$$f_{c(highpass)} = \frac{1}{2\pi R_i C_i}$$
 (4)

The value of C_i directly affects the bass (low frequency) performance of the circuit. Consider the example where R_i is 20 k Ω and the specification calls for a flat bass response down to 20 Hz. Equation 4 is reconfigured as Equation 5.

$$C_{i} = \frac{1}{2\pi R_{i} f_{c(highpass)}}$$
 (5)

In this example, C_i is 0.40 μF , so one would likely choose a value in the range of 0.47 μF to 1 μF . A further consideration for this capacitor is the leakage path from the input source through the input network formed by R_i , C_i , and the feedback resistor (R_f) to the load. This leakage current creates a dc offset voltage at the input to the amplifier that reduces useful headroom, especially in high-gain applications (gain >10). For this reason a low-leakage tantalum or ceramic capacitor is the best choice. When polarized capacitors are used, connect the positive side of the capacitor to the amplifier input in most applications. The dc level there is held at $V_{DD}/2$ —likely higher than the source dc level. It is important to confirm the capacitor polarity in the application.

POWER SUPPLY DECOUPLING, C(S)

The TPA6110A2 is a high-performance CMOS audio amplifier that requires adequate power-supply decoupling to minimize the output total harmonic distortion (THD). Power-supply decoupling also prevents oscillations when long lead lengths are used between the amplifier and the speaker. The optimum decoupling is achieved by using two capacitors of different types that target different types of noise on the power supply leads. For higher frequency transients, spikes, or digital hash on the line, a good equivalent-series-resistance (ESR) capacitor, typically 0.1 µF, placed as close as possible to the device V_{DD} lead, works best. For filtering lower-frequency noise signals, a larger aluminum electrolytic capacitor of 10 µF or greater placed near the power amplifier is recommended.

Submit Documentation Feedback



MIDRAIL BYPASS CAPACITOR, C(B)

The midrail bypass capacitor, $C_{(B)}$, serves several important functions. During start up, $C_{(B)}$ determines the rate at which the amplifier starts up. This helps to push the start-up pop noise into the subaudible range (so low it can not be heard). The second function is to reduce noise produced by the power supply caused by coupling into the output drive signal. This noise is from the midrail generation circuit internal to the amplifier. The capacitor is fed from a 230-k Ω source inside the amplifier. To keep the start-up pop as low as possible, maintain the relationship shown in Equation 6.

$$\frac{1}{\left(C_{(B)} \times 230 \text{ k}\Omega\right)} \leq \frac{1}{\left(C_{i}R_{i}\right)} \tag{6}$$

Consider an example circuit where $C_{(B)}$ is 1 μ F, C_i is 1 μ F, and R_i is 20 $k\Omega$. Substituting these values into the equation 9 results in: $6.25 \le 50$ which satisfies the rule. Bypass capacitor, $C_{(B)}$, values of 0.1 μ F to 1 μ F ceramic or tantalum low-ESR capacitors are recommended for the best THD and noise performance.

OUTPUT COUPLING CAPACITOR, C(C)

In a typical single-supply, single-ended (SE) configuration, an output coupling capacitor $(C_{(C)})$ is required to block the dc bias at the output of the amplifier, thus preventing dc currents in the load. As with the input coupling capacitor, the output coupling capacitor and impedance of the load form a high-pass filter governed by Equation 7.

$$f_{C} = \frac{1}{2\pi R_{L} C_{(C)}} \tag{7}$$

The main disadvantage, from a performance standpoint, is that the typically-small load impedance drives the low-frequency corner higher. Large values of $C_{(C)}$ are required to pass low frequencies into the load. Consider the example where a $C_{(C)}$ of 68 μF is chosen and loads vary from 32 Ω to 47 k Ω . Table 1 summarizes the frequency response characteristics of each configuration.

Table 1. Common Load Impedances vs Low-Frequency Output Characteristics in SE Mode

R _L	C _(C)	LOWEST FREQUENCY
32 Ω	68 µF	73 Hz
10,000 Ω	68 µF	0.23 Hz
47,000 Ω	68 µF	0.05 Hz

As Table 1 indicates, headphone response is adequate, and drive into line level inputs (a home stereo for example) is very good.

The output coupling capacitor required in single-supply SE mode also places additional constraints on the selection of other components in the amplifier circuit. With the rules described earlier still valid, add the following relationship:

$$\frac{1}{\left(C_{(B)} \times 230 \text{ k}\Omega\right)} \leq \frac{1}{\left(C_{i}R_{i}\right)} \ll \frac{1}{R_{L}C_{(C)}}$$
(8)

USING LOW-ESR CAPACITORS

Low-ESR capacitors are recommended throughout this application. A real capacitor can be modeled simply as a resistor in series with an ideal capacitor. The voltage drop across this resistor minimizes the beneficial effects of the capacitor in the circuit. The lower the equivalent value of this resistance, the more the real capacitor behaves like an ideal capacitor.

5-V VERSUS 3.3-V OPERATION

The TPA6110A2 was designed for operation over a supply range of 2.5 V to 5.5 V. This data sheet provides full specifications for 5-V and 3.3-V operation, since these are considered to be the two most common supply voltages. There are no special considerations for 3.3-V versus 5-V operation as far as supply bypassing, gain setting, or stability. The most important consideration is that of output power. Each amplifier in theTPA6110A2 can produce a maximum voltage swing of $V_{DD}-1$ V. This means, for 3.3-V operation, clipping starts to occur when $V_{O(PP)}=2.3$ V as opposed when $V_{O(PP)}=4$ V while operating at 5 V. The reduced voltage swing subsequently reduces maximum output power into the load before distortion becomes significant.



REVISION HISTORY

CI	nanges from Original (December 2000) to Revision A	Page
•	Change the DC ELECTRICAL CHARACTERISTICS table From T_A = 25°C, V_{DD} = 3.3 V To: T_A = 25°C, V_{DD} = 2.5 V, updated values	
•	Change the DC ELECTRICAL CHARACTERISTICS table From $T_A = 25^{\circ}C$, $V_{DD} = 5$ V To: $T_A = 25^{\circ}C$, $V_{DD} = 5.5$ V, updated values	3
•	Changed Figure 8, From: $R_L = 8k\Omega$ To: $R_L = 8\Omega$	<u>6</u>
•	Changed Figure 24, From: frequency limit at 1M To: frequency limit at 20K	10
<u>.</u>	Changed Figure 25, From: frequency limit at 1M To: frequency limit at 20K	11
CI	nanges from Revision A (September 2004) to Revision B	Page
	Changed the DC Electrical Characteristice ($V_{DD} = 2.5V$) for $I_{DD(SD)}$ From: Typ = 10 Max = 50 To: Typ = 1 Max = 10 .	3
•	Changed the DC Electrical Characteristice ($V_{DD} = 5.5V$) for $I_{DD(SD)}$ From: Typ = 60 Max = 100 To: Typ = 1 Max = 10	3





28-Apr-2011

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/ Ball Finish	MSL Peak Temp ⁽³⁾	Samples (Requires Login)
TPA6110A2DGN	ACTIVE	MSOP- PowerPAD	DGN	8	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TPA6110A2DGNG4	ACTIVE	MSOP- PowerPAD	DGN	8	80	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TPA6110A2DGNR	ACTIVE	MSOP- PowerPAD	DGN	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TPA6110A2DGNRG4	ACTIVE	MSOP- PowerPAD	DGN	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes. **Pb-Free** (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

PACKAGE MATERIALS INFORMATION

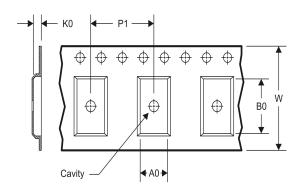
www.ti.com 4-May-2012

TAPE AND REEL INFORMATION

REEL DIMENSIONS



TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

TAPE AND REEL INFORMATION

*All dimensions are nominal

Device		Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPA6110A2DGNR	MSOP- Power PAD	DGN	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
TPA6110A2DGNR	MSOP- Power PAD	DGN	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1

www.ti.com 4-May-2012



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPA6110A2DGNR	MSOP-PowerPAD	DGN	8	2500	358.0	335.0	35.0
TPA6110A2DGNR	MSOP-PowerPAD	DGN	8	2500	364.0	364.0	27.0

DGN (S-PDSO-G8)

PowerPAD™ PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com www.ti.com.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- F. Falls within JEDEC MO-187 variation AA-T

PowerPAD is a trademark of Texas Instruments.



DGN (S-PDSO-G8)

PowerPAD™ PLASTIC SMALL OUTLINE

THERMAL INFORMATION

This PowerPAD $^{\text{M}}$ package incorporates an exposed thermal pad that is designed to be attached to a printed circuit board (PCB). The thermal pad must be soldered directly to the PCB. After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For additional information on the PowerPAD package and how to take advantage of its heat dissipating abilities, refer to Technical Brief, PowerPAD Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD Made Easy, Texas Instruments Literature No. SLMA004. Both documents are available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Exposed Thermal Pad Dimensions

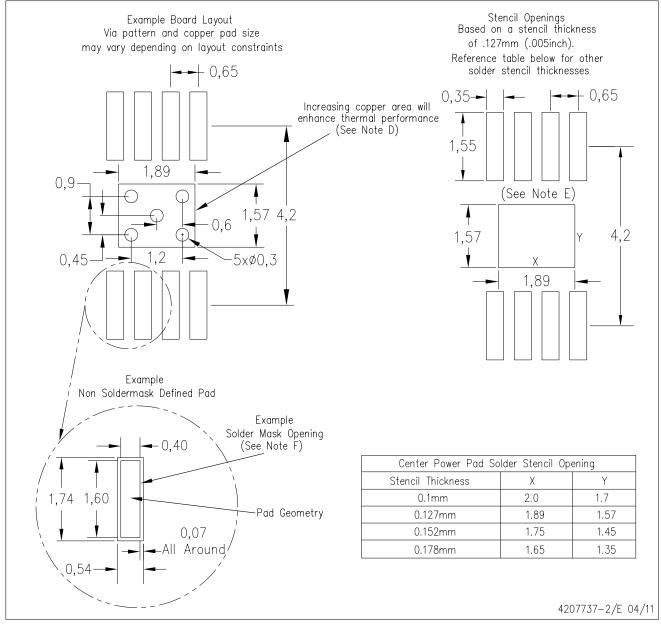
4206323-2/1 12/11

NOTE: All linear dimensions are in millimeters



DGN (R-PDSO-G8)

PowerPADTM PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002, SLMA004, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com www.ti.com. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.
- F. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

PowerPAD is a trademark of Texas Instruments



IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, modifications, enhancements, improvements, and other changes to its products and services at any time and to discontinue any product or service without notice. Customers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All products are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its hardware products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by government requirements, testing of all parameters of each product is not necessarily performed.

TI assumes no liability for applications assistance or customer product design. Customers are responsible for their products and applications using TI components. To minimize the risks associated with customer products and applications, customers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any TI patent right, copyright, mask work right, or other TI intellectual property right relating to any combination, machine, or process in which TI products or services are used. Information published by TI regarding third-party products or services does not constitute a license from TI to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. Reproduction of this information with alteration is an unfair and deceptive business practice. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI products or services with statements different from or beyond the parameters stated by TI for that product or service voids all express and any implied warranties for the associated TI product or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

TI products are not authorized for use in safety-critical applications (such as life support) where a failure of the TI product would reasonably be expected to cause severe personal injury or death, unless officers of the parties have executed an agreement specifically governing such use. Buyers represent that they have all necessary expertise in the safety and regulatory ramifications of their applications, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of TI products in such safety-critical applications, notwithstanding any applications-related information or support that may be provided by TI. Further, Buyers must fully indemnify TI and its representatives against any damages arising out of the use of TI products in such safety-critical applications.

TI products are neither designed nor intended for use in military/aerospace applications or environments unless the TI products are specifically designated by TI as military-grade or "enhanced plastic." Only products designated by TI as military-grade meet military specifications. Buyers acknowledge and agree that any such use of TI products which TI has not designated as military-grade is solely at the Buyer's risk, and that they are solely responsible for compliance with all legal and regulatory requirements in connection with such use.

Applications

Automotive and Transportation www.ti.com/automotive

e2e.ti.com

TI products are neither designed nor intended for use in automotive applications or environments unless the specific TI products are designated by TI as compliant with ISO/TS 16949 requirements. Buyers acknowledge and agree that, if they use any non-designated products in automotive applications, TI will not be responsible for any failure to meet such requirements.

Following are URLs where you can obtain information on other Texas Instruments products and application solutions:

		•	
Amplifiers	amplifier.ti.com	Communications and Telecom	www.ti.com/communications
Data Converters	dataconverter.ti.com	Computers and Peripherals	www.ti.com/computers
DLP® Products	www.dlp.com	Consumer Electronics	www.ti.com/consumer-apps
DSP	dsp.ti.com	Energy and Lighting	www.ti.com/energy
Clocks and Timers	www.ti.com/clocks	Industrial	www.ti.com/industrial
Interface	interface.ti.com	Medical	www.ti.com/medical
Logic	logic.ti.com	Security	www.ti.com/security
Power Mgmt	power.ti.com	Space, Avionics and Defense	www.ti.com/space-avionics-defense
Microcontrollers	microcontroller.ti.com	Video and Imaging	www.ti.com/video

RFID <u>www.ti-rfid.com</u>
OMAP Mobile Processors www.ti.com/omap

Products

Audio

Wireless Connectivity www.ti.com/wirelessconnectivity

www.ti.com/audio

TI E2E Community Home Page

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2012, Texas Instruments Incorporated